



VDRM SERIES

2.5 to 16kV, 50 to 125mA, 200nS
Axial Lead Low Current Diodes

Features

- Low Power
- Miniature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material



Specifications¹

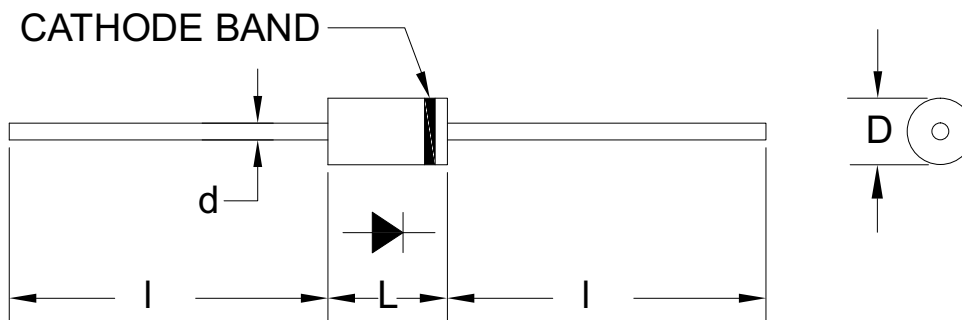
Part Number	V _{RRM} V	I _{FAVM} mA	V _F ² V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
VDRM25	2500	125	4	0.1	12	3.0	200	0.32	0.12	0.025	1.0
VDRM50	5000	100	8	0.1	10	1.5	200	0.32	0.12	0.025	1.0
VDRM100	10000	75	14	0.1	5	0.8	200	0.32	0.12	0.025	1.0
VDRM160	16000	50	19	0.1	4	0.5	200	0.32	0.12	0.025	1.0

Temperature °C	
Operating Temperature	-55 to 150 (VDRM25 to VDRM100) -55 to 125 (VDRM160)
Storage Temperature	-55 to 175
Maximum Junction Temperature	150 (VDRM25 to VDRM100) 125 (VDRM160)

¹25°C ambient temperature unless stated otherwise.

²Check Specifications Definitions for conditions details.

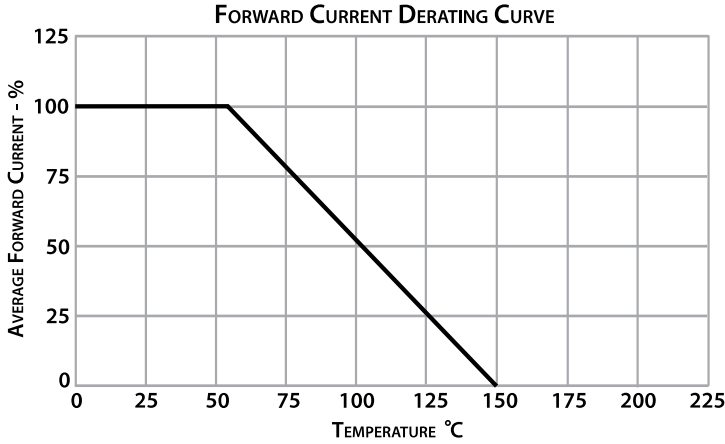
Drawings



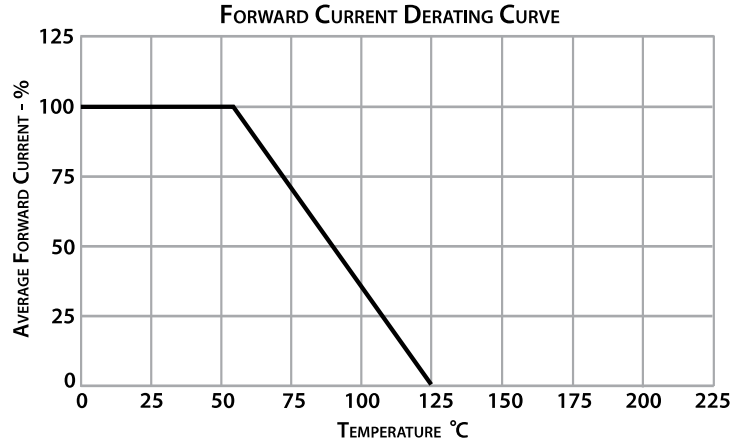
Dimensions in inches, tolerances ±0.020 except as noted



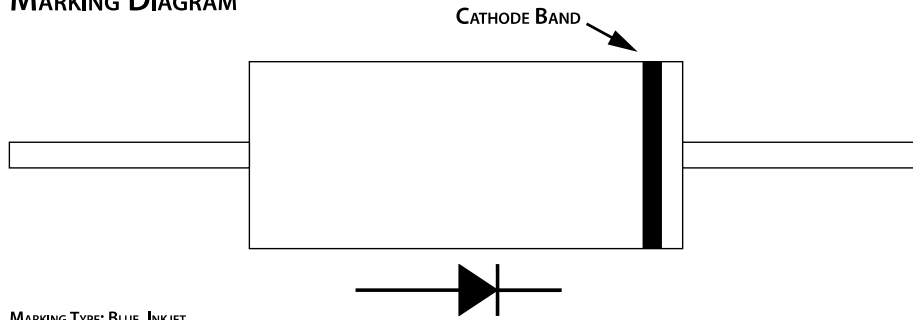
VDRM25 to VDRM100



VDRM160



MARKING DIAGRAM



MARKING TYPE: BLUE, INKJET
(MARKINGS WILL WRAP ENTIRE BODY OF DIODE AND ARE SUBJECT TO MINOR CHANGES)

Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At 25mA (VDRM25 to VDRM100) At 10mA (VDRM160)
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 12.5mA; I _R = -25mA; I _{RR} = -6.3mA

Note: Specifications subject to change without notice. Photo is representation only.

